

Performance

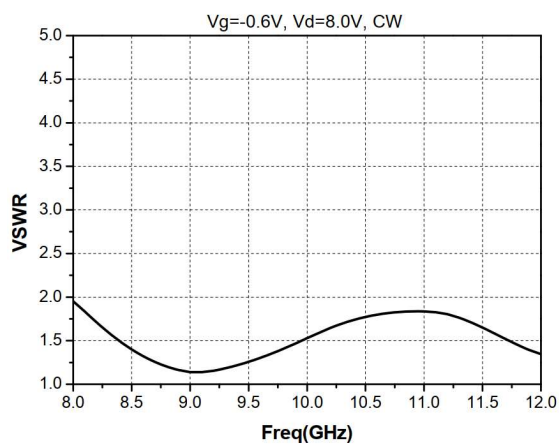
- Frequency: 8.0~12.0GHz
- Linear Gain: 25dB
- Saturation Output Power: 41.3dBm
- Power Added Efficiency: 37%
- Bias Condition: 8V, -0.6V
- Size: 3.2*4.0mm*0.08mm
- Process: 0.35um PHEMT Technology

Electrical Specifications (Vd=8V, Vg= -0.6V, Freq=8.0~12.0GHz)

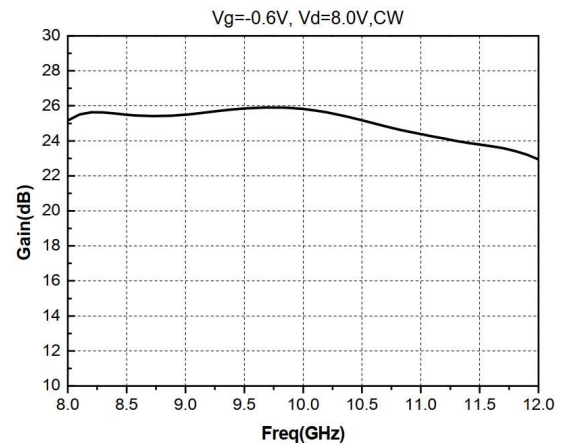
Symbol	Parameter	Min	Typical	Max	Unit
Psat	Saturated Output Power		41.3	-	dBm
PAE	Power Added Efficiency		37	-	%
GP	Saturated Power Gain		19	-	dB
G	Linear Gain		25	-	dB
R _{θj}	Thermal Resistance (Vd=8V, Id=3A)		1.8		°C/W

Test Curves

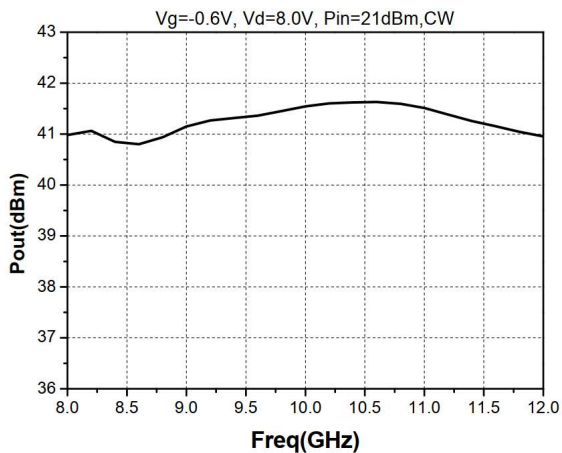
VSWR vs. Freq



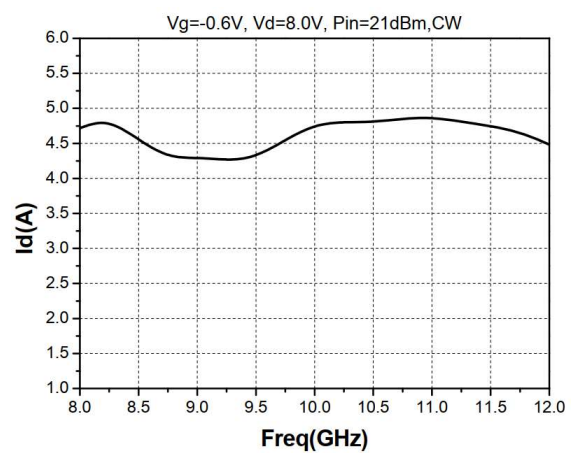
Linear Gain vs. Freq

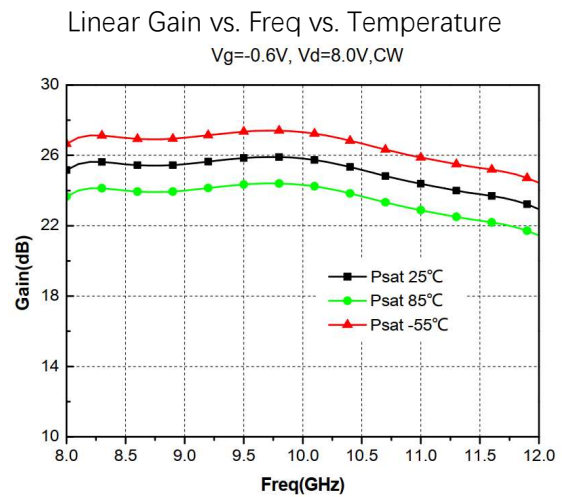
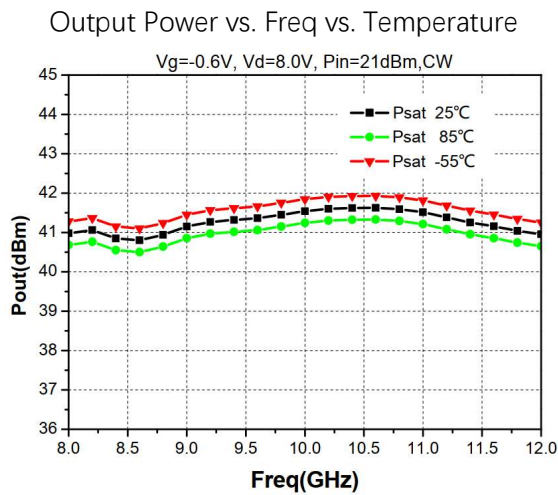
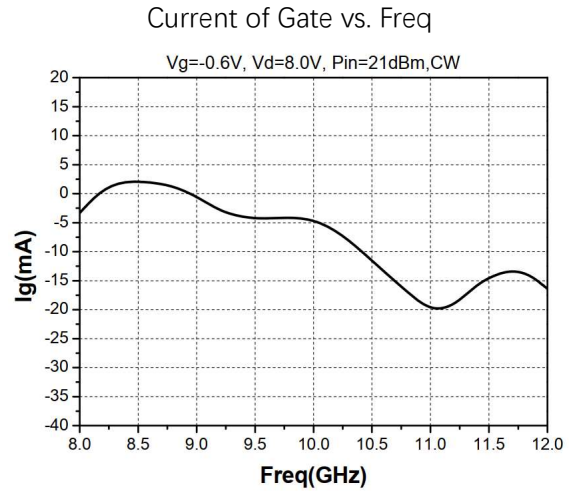
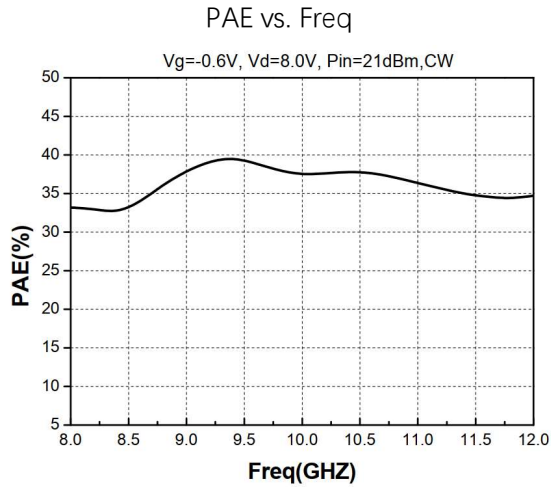


Output Power vs. Freq



Drain Current vs. Freq





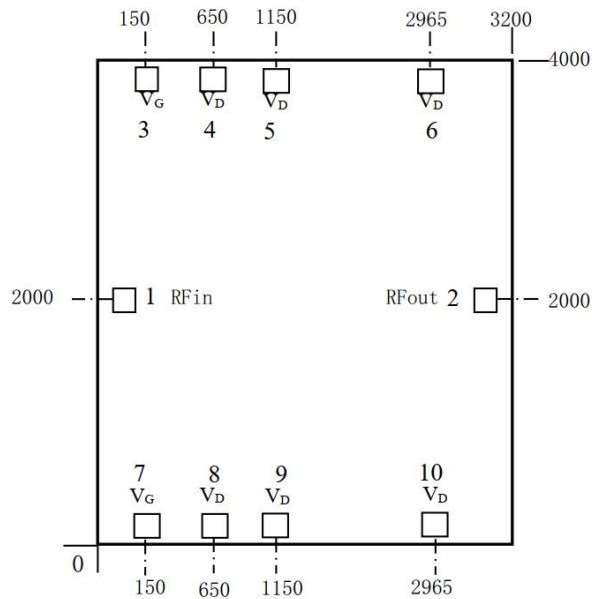
Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	9V	
Id	Drain Current	6A	
Vg	Gate Voltage	-0.45V	
Ig	Gate Current	100mA	
Pd	DC Power Consumption	45W	
Pin	Input Power	28dBm	
Tch	Channel Temperature	150°C	
Tm	Mounting Temperature	300°C	1 min, N2 Protection
Tstg	Storage Temperature	-55~150°C	

Exceeding any one or combination of these limits may cause permanent damage.

Outline Size (mm)

Assembly Diagram



Assembly Diagram

